MJD2955 (PNP), MJD3055 (NPN)

Complementary Power Transistors

DPAK for Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Electrically Similar to MJE2955 and MJE3055
- High Current Gain–Bandwidth Product
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector–Emitter Voltage	V _{CEO}	60	Vdc
Collector-Base Voltage	V _{CB}	70	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
Collector Current	۱ _C	10	Adc
Base Current	Ι _Β	6	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D †	20 0.16	W W/°C
Total Power Dissipation (Note 1) @ $T_A = 25^{\circ}C$ Derate above 25°C	PD	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

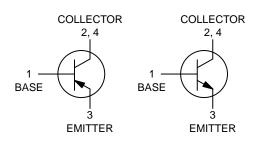


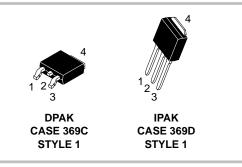
ON Semiconductor®

http://onsemi.com

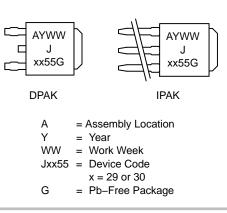
SILICON POWER TRANSISTORS 10 AMPERES 60 VOLTS, 20 WATTS







MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MJD2955 (PNP), MJD3055 (NPN)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ extsf{ heta}JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	71.4	°C/W

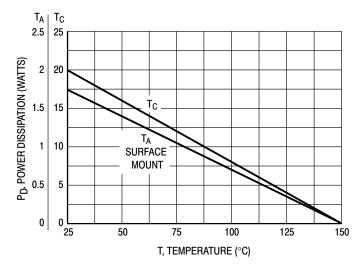
2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				ł
Collector-Emitter Sustaining Voltage (Note 3) $(I_C = 30 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	60	-	Vdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}, I_B = 0$)	I _{CEO}	_	50	μAdc
Collector Cutoff Current ($V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}$) ($V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_C = 150^{\circ}C$)	ICEX		0.02 2	mAdc
Collector Cutoff Current ($V_{CB} = 70 \text{ Vdc}, I_E = 0$) ($V_{CB} = 70 \text{ Vdc}, I_E = 0, T_C = 150^{\circ}C$)	I _{CBO}		0.02 2	mAdc
Emitter Cutoff Current ($V_{BE} = 5 \text{ Vdc}, I_C = 0$)	I _{EBO}	_	0.5	mAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) ($I_C = 4 \text{ Adc}, V_{CE} = 4 \text{ Vdc}$) ($I_C = 10 \text{ Adc}, V_{CE} = 4 \text{ Vdc}$)	h _{FE}	20 5	100	_
Collector–Emitter Saturation Voltage (Note 3) ($I_C = 4 \text{ Adc}, I_B = 0.4 \text{ Adc}$) ($I_C = 10 \text{ Adc}, I_B = 3.3 \text{ Adc}$)	V _{CE(sat)}		1.1 8	Vdc
Base-Emitter On Voltage (Note 3) (I _C = 4 Adc, V _{CE} = 4 Vdc)	V _{BE(on)}	_	1.8	Vdc
DYNAMIC CHARACTERISTICS			•	•
Current–Gain – Bandwidth Product (I _C = 500 mAdc, V _{CE} = 10 Vdc, f = 500 kHz)	f _T	2	_	MHz

3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS





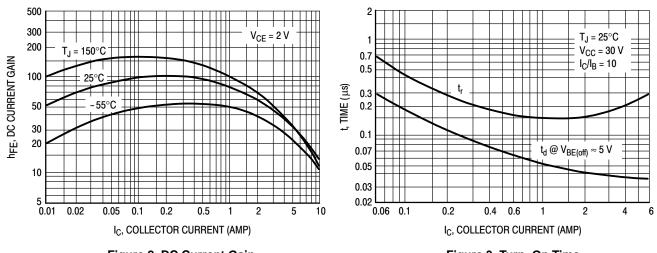
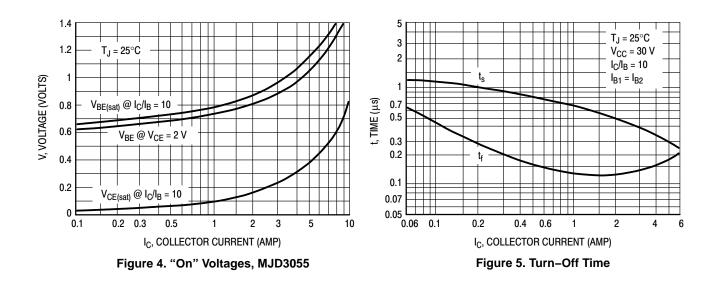




Figure 3. Turn–On Time



MJD2955 (PNP), MJD3055 (NPN)

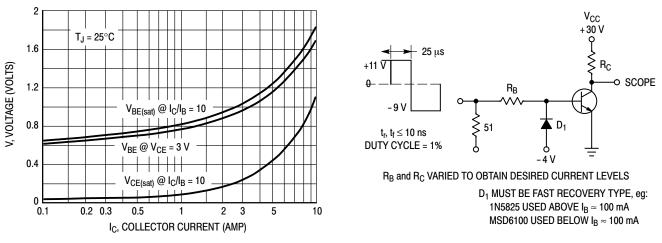
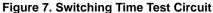
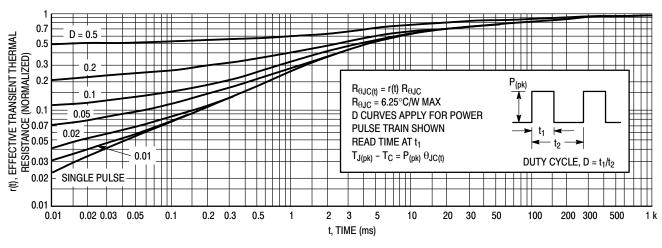
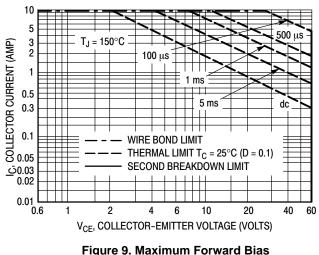


Figure 6. "On" Voltages, MJD2955









Safe Operating Area

Forward Bias Safe Operating Area Information

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on $T_{J(pk)} = 150^{\circ}$ C; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}$ C. $T_{J(pk)}$ may be calculated from the data in Figure 8. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

MJD2955 (PNP), MJD3055 (NPN)

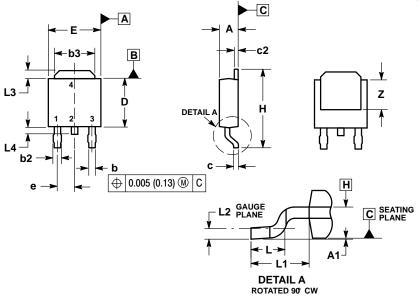
ORDERING INFORMATION

Device	Package Type	Package	Shipping [†]
MJD2955G	DPAK (Pb–Free)	369C	75 Units / Rail
MJD2955–1G	IPAK (Pb–Free)	369D	75 Units / Rail
MJD2955T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD2955T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD3055G	JD3055G DPAK (Pb–Free)		75 Units / Rail
MJD3055T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD3055T4G*	DPAK (Pb–Free)	369C	2,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 *NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE) CASE 369C ISSUE D



NOTES:

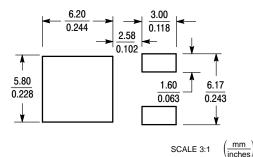
- NOTES:
 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: INCHES.
 THERMAL PAD CONTOUR OPTIONAL WITHIN DI-MENSIONS b3, L3 and Z.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 DATUMS A AND B ARE DETERMINED AT DATUM
- 6. DATUMS A AND B ARE DETERMINED AT DATUM

PLANE H.					
	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.086	0.094	2.18	2.38	
A1	0.000	0.005	0.00	0.13	
b	0.025	0.035	0.63	0.89	
b2	0.030	0.045	0.76	1.14	
b3	0.180	0.215	4.57	5.46	
С	0.018	0.024	0.46	0.61	
c2	0.018	0.024	0.46	0.61	
D	0.235	0.245	5.97	6.22	
Е	0.250	0.265	6.35	6.73	
е	0.090 BSC		2.29 BSC		
Н	0.370	0.410	9.40	10.41	
L	0.055	0.070	1.40	1.78	
L1	0.108 REF		2.74	REF	
L2	0.020 BSC		0.51 BSC		
L3	0.035	0.050	0.89	1.27	
L4		0.040		1.01	
Ζ	0.155		3.93		

STYLE 1: PIN 1. BASE

2. COLLECTOR 3. EMITTER 4. COLLECTOR

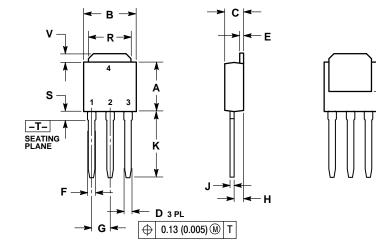
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
ĸ	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
v	0.035	0.050	0.89	1.27
Z	0.155		3.93	

STYLE 1: PIN 1. BASE

z

2. COLLECTOR EMITTER 3.

COLLECTOR

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